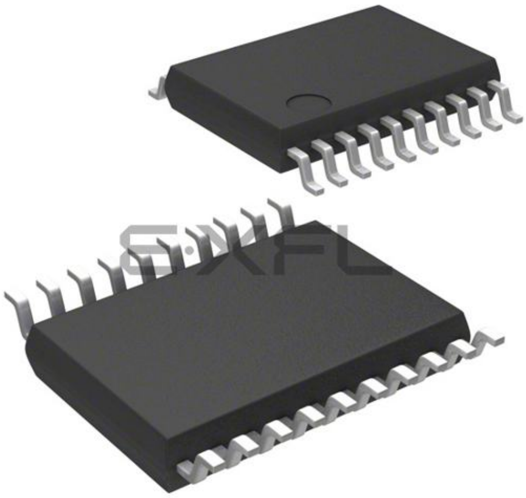

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	16
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	20-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f042f6p7

List of tables

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F042x4/x6 microcontrollers.

This document should be read in conjunction with the STM32F0xxxx reference manual (RM0091). The reference manual is available from the STMicroelectronics website www.st.com.

For information on the ARM® Cortex®-M0 core, please refer to the Cortex®-M0 Technical Reference Manual, available from the www.arm.com website.

3 Functional overview

Figure 1 shows the general block diagram of the STM32F042x4/x6 devices.

3.1 ARM®-Cortex®-M0 core

The ARM® Cortex®-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM® Cortex®-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F042x4/x6 devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 6 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
  - 16 to 32 Kbytes of embedded Flash memory for programs and data
  - Option bytes

  The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:
  - Level 0: no readout protection
  - Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
  - Level 2: chip readout protection, debug features (Cortex®-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bits are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot pin is shared with the standard GPIO and can be disabled through the boot selector option bits. The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15, or PA9/PA10 or I²C on pins PB6/PB7 or through the USB DFU interface.

Table 6. No. of capacitive sensing channels available on STM32F042x devices

Analog I/O group	Number of capacitive sensing channels				
	STM32F042Cx LQPF48 UQFPN48	STM32F042Tx WLCSP36	STM32F042Kx LQFP32 UQFPN32	STM32F042Gx UQFPN28	STM32F042Fx TSSOP20
G1	3	3	3	3	3
G2	3	3	3	3	3
G3	2	2	1 2	1	0
G4	3	3	3	1	1
G5	3	3	3	3	0
Number of capacitive sensing channels	14	14	13 14	11	7

3.12 Timers and watchdogs

The STM32F042x4/x6 devices include up to five general-purpose timers and an advanced control timer.

Table 7 compares the features of the different timers.

Table 7. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	3
General purpose	TIM2	32-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM14	16-bit	Up	integer from 1 to 65536	No	1	-
	TIM16 TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	1

3.12.1 Advanced-control timer (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on six channels. It has complementary PWM outputs with programmable inserted dead times. It can also be seen as a complete general-purpose timer. The four independent channels can be used for:

- input capture
- output compare
- PWM generation (edge or center-aligned modes)
- one-pulse mode output

If configured as a standard 16-bit timer, it has the same features as the TIMx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

The counter can be frozen in debug mode.

Many features are shared with those of the standard timers which have the same architecture. The advanced control timer can therefore work together with the other timers via the Timer Link feature for synchronization or event chaining.

3.12.2 General-purpose timers (TIM2, 3, 14, 16, 17)

There are five synchronizable general-purpose timers embedded in the STM32F042x4/x6 devices (see *Table 7* for differences). Each general-purpose timer can be used to generate PWM outputs, or as simple time base.

TIM2, TIM3

STM32F042x4/x6 devices feature two synchronizable 4-channel general-purpose timers. TIM2 is based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. TIM3 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2 and TIM3 general-purpose timers can work together or with the TIM1 advanced-control timer via the Timer Link feature for synchronization or event chaining.

TIM2 and TIM3 both have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Their counters can be frozen in debug mode.

TIM14

This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM14 features one single channel for input capture/output compare, PWM or one-pulse mode output.

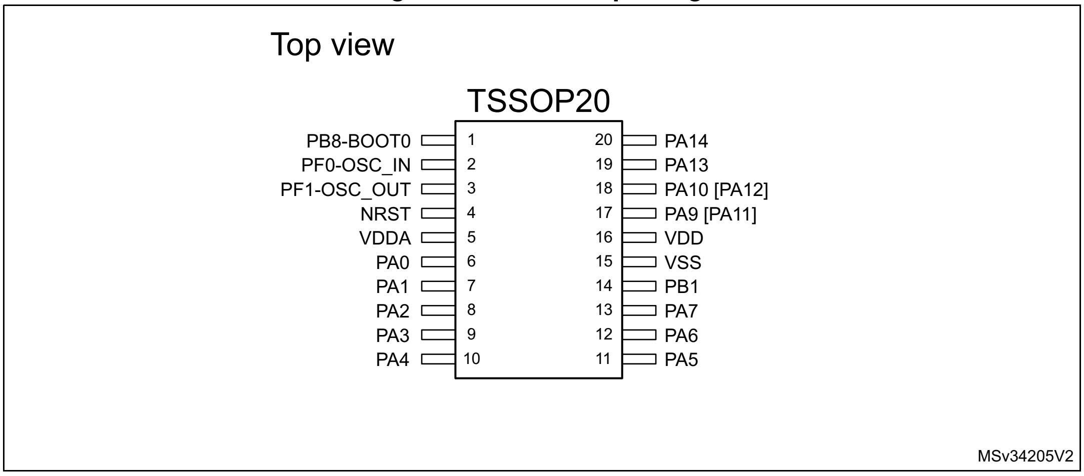
Its counter can be frozen in debug mode.

TIM16 and TIM17

Both timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

They each have a single channel for input capture/output compare, PWM or one-pulse mode output.

Figure 9. TSSOP20 package



1. Pin pair PA11/12 can be remapped in place of pin pair PA9/10 using the SYSCFG_CFGR1 register.

Table 12. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I/O	Input / output pin
I/O structure	FT	5 V-tolerant I/O
	FTf	5 V-tolerant I/O, FM+ capable
	TTa	3.3 V-tolerant I/O directly connected to ADC
	TC	Standard 3.3 V I/O
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers
	Additional functions	Functions directly selected/enabled through peripheral registers

Table 22. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 23* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

Table 23. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{POR/PDR}$(1)	Power on/power down reset threshold	Falling edge(2)	1.80	1.88	1.96(3)	V
		Rising edge	1.84(3)	1.92	2.00	V
$V_{PDRhyst}$	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}$(4)	Reset temporization	-	1.50	2.50	4.50	ms

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
3. Data based on characterization results, not tested in production.
4. Guaranteed by design, not tested in production.

Table 24. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	V
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	V
		Falling edge	2.09	2.18	2.27	V
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	V
		Falling edge	2.18	2.28	2.38	V
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	V
		Falling edge	2.28	2.38	2.48	V
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	V
		Falling edge	2.37	2.48	2.59	V
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	V
		Falling edge	2.47	2.58	2.69	V

Table 30. Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal

Symbol	Parameter	f_{HCLK}	Typical consumption in Run mode		Typical consumption in Sleep mode		Unit
			Peripherals enabled	Peripherals disabled	Peripherals enabled	Peripherals disabled	
I_{DD}	Current consumption from V_{DD} supply	48 MHz	20.7	12.8	12.3	3.4	mA
		36 MHz	15.9	9.9	9.5	2.7	
		32 MHz	14.3	9.0	8.5	2.5	
		24 MHz	11.0	7.1	6.6	2.1	
		16 MHz	7.7	5.0	4.7	1.6	
		8 MHz	4.3	3.0	2.7	1.2	
		4 MHz	2.6	2.0	1.7	0.9	
		2 MHz	1.8	1.5	1.2	0.8	
		1 MHz	1.4	1.2	1.0	0.8	
		500 kHz	1.2	1.1	0.8	0.7	
I_{DDA}	Current consumption from V_{DDA} supply	48 MHz	163.3				μA
		36 MHz	124.3				
		32 MHz	111.9				
		24 MHz	87.1				
		16 MHz	62.5				
		8 MHz	2.5				
		4 MHz	2.5				
		2 MHz	2.5				
		1 MHz	2.5				
		500 kHz	2.5				

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 50: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt

Table 31. Switching output I/O current consumption

Symbol	Parameter	Conditions[1]	I/O toggling frequency (f_{SW})	Typ	Unit
I_{SW}	I/O current consumption	V_{DDIOx} = 3.3 V C = C_{INT}	4 MHz	0.07	mA
			8 MHz	0.15	
			16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
		V_{DDIOx} = 3.3 V C_{EXT} = 0 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.18	
			8 MHz	0.37	
			16 MHz	0.76	
			24 MHz	1.39	
			48 MHz	2.188	
		V_{DDIOx} = 3.3 V C_{EXT} = 10 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.32	
			8 MHz	0.64	
			16 MHz	1.25	
			24 MHz	2.23	
			48 MHz	4.442	
		V_{DDIOx} = 3.3 V C_{EXT} = 22 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
		V_{DDIOx} = 3.3 V C_{EXT} = 33 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.64	
			8 MHz	1.25	
			16 MHz	3.24	
			24 MHz	5.02	
		V_{DDIOx} = 3.3 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.81	
			8 MHz	1.7	
			16 MHz	3.67	
		V_{DDIOx} = 2.4 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.66	
			8 MHz	1.43	
			16 MHz	2.45	
			24 MHz	4.97	

1. C_S = 7 pF (estimated value).

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 36*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 36. HSE oscillator characteristics

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.4	-	
		V_{DD} = 3.3 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.5	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design, not tested in production.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Low-speed internal (LSI) RC oscillator

Table 41. LSI oscillator characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DDA(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 42* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*.

Table 42. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
f_{PLL_IN}	PLL input clock(1)	1(2)	8.0	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	48	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
$Jitter_{PLL}$	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = - 40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (1 KB) erase time	T_A = - 40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = - 40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 49. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on PA12 pin	-0	+5	mA
	Injected current on PA9, PB3, PB13, PF11 pins with induced leakage current on adjacent pins less than 50 µA	-5	NA	
	Injected current on PB0, PB1 and all other FT and FTf pins	-5	NA	
	Injected current on all other TC, TTa and RST pins	-5	+5	

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the conditions summarized in *Table 21: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant.

Table 50. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	$0.3\ V_{DDIOx}+0.07$(1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DDIOx}-0.2$(1)	
		All I/Os	-	-	$0.3\ V_{DDIOx}$	
V_{IH}	High level input voltage	TC and TTa I/O	$0.445\ V_{DDIOx}+0.398$(1)	-	-	V
		FT and FTf I/O	$0.5\ V_{DDIOx}+0.2$(1)	-	-	
		All I/Os	$0.7\ V_{DDIOx}$	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200(1)	-	mV
		FT and FTf I/O	-	100(1)	-	
I_{lkg}	Input leakage current(2)	TC, FT and FTf I/O TTa in digital mode $V_{SS} \leq V_{IN} \leq V_{DDIOx}$	-	-	± 0.1	µA
		TTa in digital mode $V_{DDIOx} \leq V_{IN} \leq V_{DDA}$	-	-	1	
		TTa in analog mode $V_{SS} \leq V_{IN} \leq V_{DDA}$	-	-	± 0.2	
		FT and FTf I/O $V_{DDIOx} \leq V_{IN} \leq 5\ V$	-	-	10	
R_{PU}	Weak pull-up equivalent resistor (3)	$V_{IN} = V_{SS}$	25	40	55	kΩ

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to +/-8 mA, and sink or source up to +/- 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V_{DDIOx}, plus the maximum consumption of the MCU sourced on V_{DD}, cannot exceed the absolute maximum rating ΣI_{VDD} (see *Table 18: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V_{SS}, plus the maximum consumption of the MCU sunk on V_{SS}, cannot exceed the absolute maximum rating ΣI_{VSS} (see *Table 18: Voltage characteristics*).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 21: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT, TTa or TC unless otherwise specified).

Table 51. Output voltage characteristics(1)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port(2) $\lvert I_{IO}\rvert$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OL}	Output low level voltage for an I/O pin	TTL port(2) $\lvert I_{IO}\rvert$ = 8 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		2.4	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\lvert I_{IO}\rvert$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	1.3	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–1.3	-	
V_{OL}(3)	Output low level voltage for an I/O pin	$\lvert I_{IO}\rvert$ = 6 mA $V_{DDIOx} \geq 2$ V	-	0.4	V
V_{OH}(3)	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	
V_{OL}(4)	Output low level voltage for an I/O pin	$\lvert I_{IO}\rvert$ = 4 mA	-	0.4	V
V_{OH}(4)	Output high level voltage for an I/O pin		V_{DDIOx}–0.4	-	V
V_{OLFm+}(3)	Output low level voltage for an FTf I/O pin in Fm+ mode	$\lvert I_{IO}\rvert$ = 20 mA $V_{DDIOx} \geq 2.7$ V	-	0.4	V
		$\lvert I_{IO}\rvert$ = 10 mA	-	0.4	V

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in *Table 18: Voltage characteristics*, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO}.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. Data based on characterization results. Not tested in production.
4. Data based on characterization results. Not tested in production.

Table 54. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{TRIG}(2)	External trigger frequency	f_{ADC} = 14 MHz, 12-bit resolution	-	-	823	kHz
		12-bit resolution	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range	-	0	-	V_{DDA}	V
R_{AIN}(2)	External input impedance	See Equation 1 and Table 55 for details	-	-	50	kΩ
R_{ADC}(2)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(2)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(2)(3)	Calibration time	f_{ADC} = 14 MHz	5.9			µs
		-	83			$1/f_{ADC}$
$W_{LATENCY}$(2)(4)	ADC_DR register ready latency	ADC clock = HSI14	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr}(2)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2$ = 14 MHz	0.196			µs
		$f_{ADC} = f_{PCLK}/2$	5.5			$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4$ = 12 MHz	0.219			µs
		$f_{ADC} = f_{PCLK}/4$	10.5			$1/f_{PCLK}$
		$f_{ADC} = f_{HSI14}$ = 14 MHz	0.179	-	0.250	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI14}$	-	1	-	$1/f_{HSI14}$
t_S(2)	Sampling time	f_{ADC} = 14 MHz	0.107	-	17.1	µs
		-	1.5	-	239.5	$1/f_{ADC}$
t_{STAB}(2)	Stabilization time	-	14			$1/f_{ADC}$
t_{CONV}(2)	Total conversion time (including sampling time)	f_{ADC} = 14 MHz, 12-bit resolution	1	-	18	µs
		12-bit resolution	14 to 252 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

1. During conversion of the sampled value (12.5 x ADC clock period), an additional consumption of 100 µA on I_{DDA} and 60 µA on I_{DD} should be taken into account.
2. Guaranteed by design, not tested in production.
3. Specified value includes only ADC timing. It does not include the latency of the register access.
4. This parameter specify latency for transfer of the conversion result to the ADC_DR register. EOC flag is set at this time.

Figure 28. SPI timing diagram - slave mode and CPHA = 0

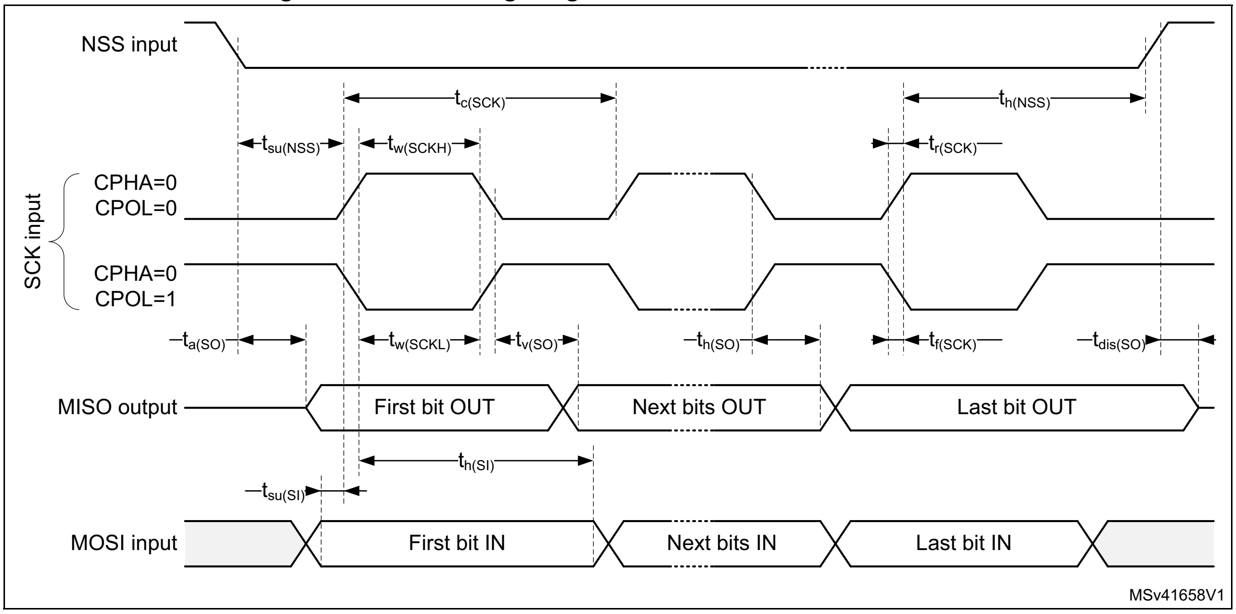
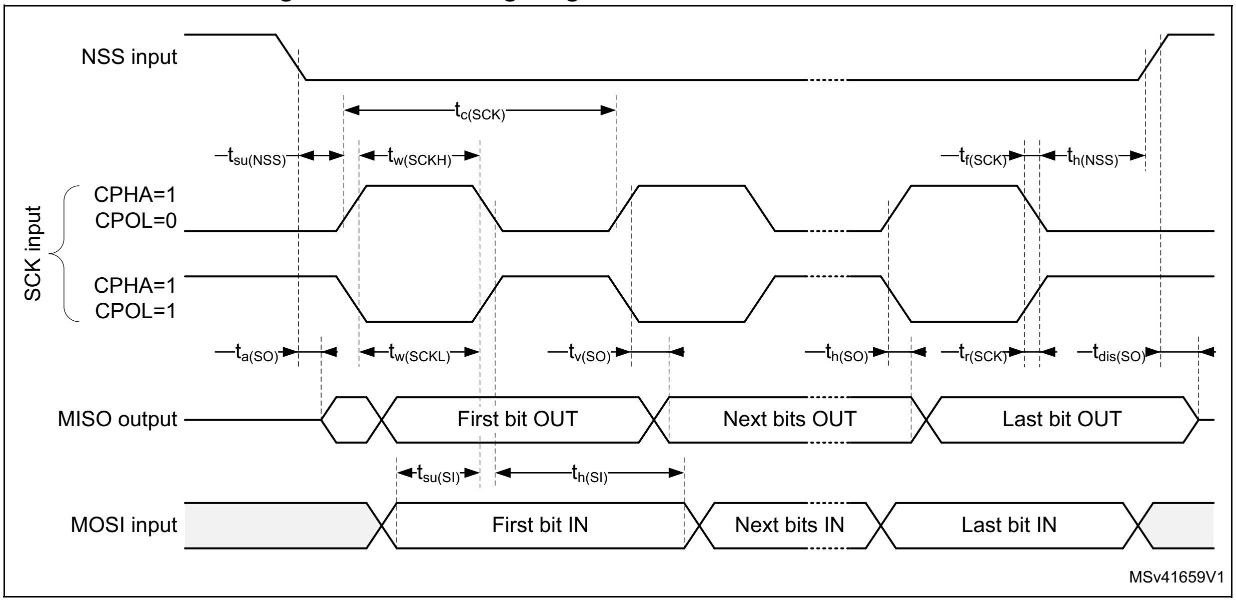


Figure 29. SPI timing diagram - slave mode and CPHA = 1



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

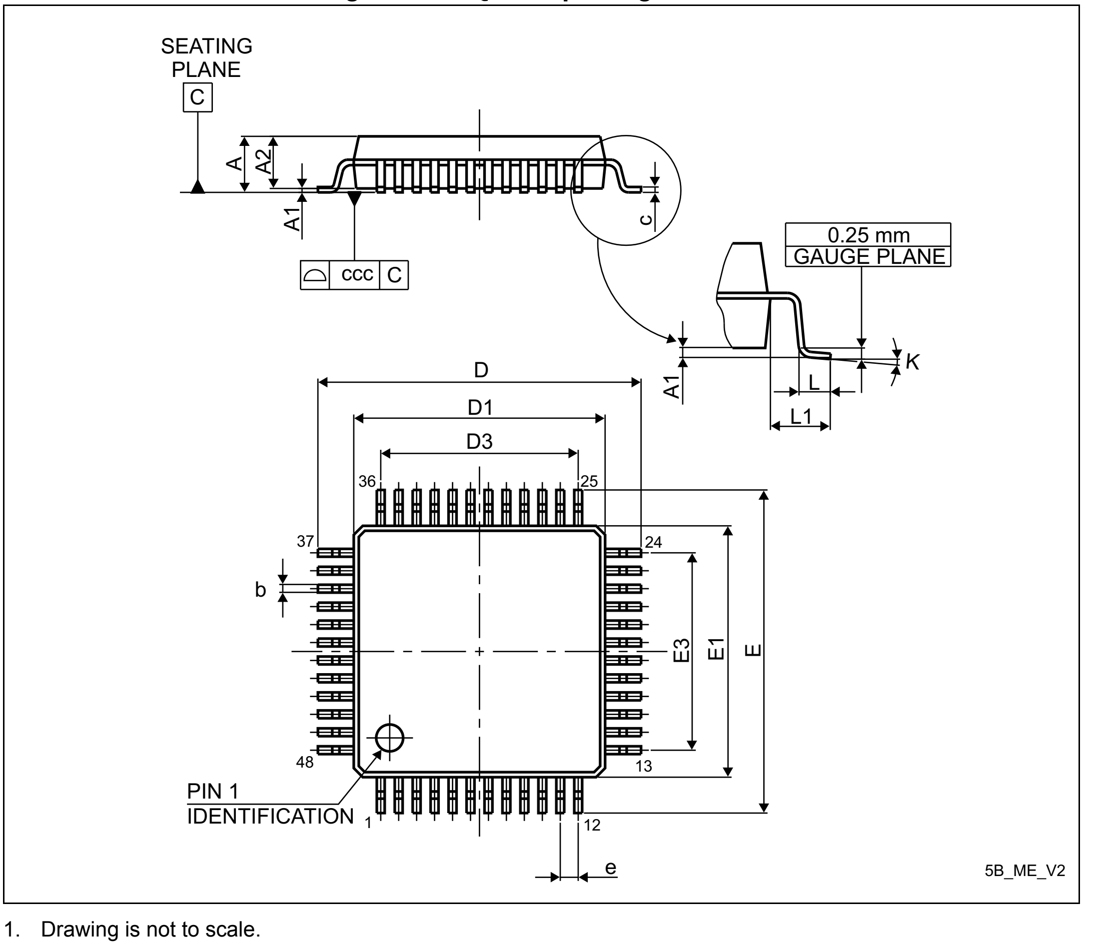
7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

7.1 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7 mm low-profile quad flat package.

Figure 33. LQFP48 package outline

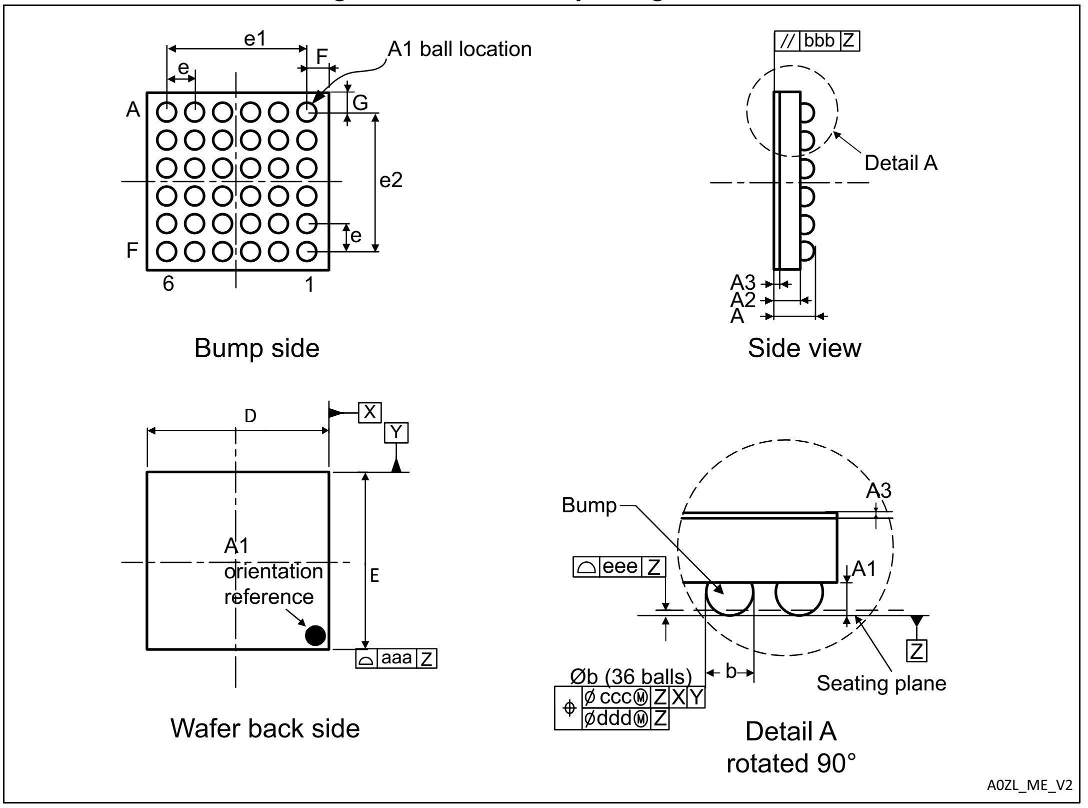


1. Drawing is not to scale.

7.3 WLCSP36 package information

WLCSP36 is a 36-ball, 2.605 x 2.703 mm, 0.4 mm pitch wafer-level chip-scale package.

Figure 39. WLCSP36 package outline

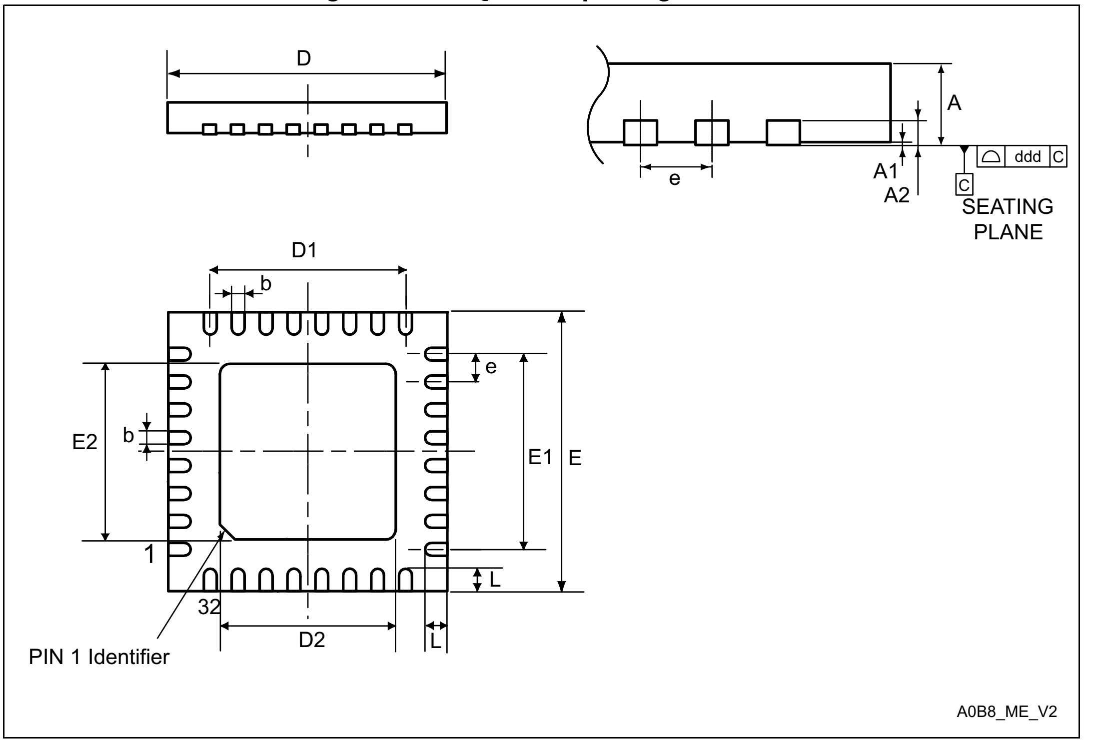


1. Drawing is not to scale.

Table 68. WLCSP36 package mechanical data

Symbol	millimeters			inches[(1)]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[(2)]	-	0.025	-	-	0.0010	-
b[(3)]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.570	2.605	2.640	0.1012	0.1026	0.1039
E	2.668	2.703	2.738	0.1050	0.1064	0.1078
e	-	0.400	-	-	0.0157	-
e1	-	2.000	-	-	0.0787	-
e2	-	2.000	-	-	0.0787	-

Figure 45. UFQFPN32 package outline



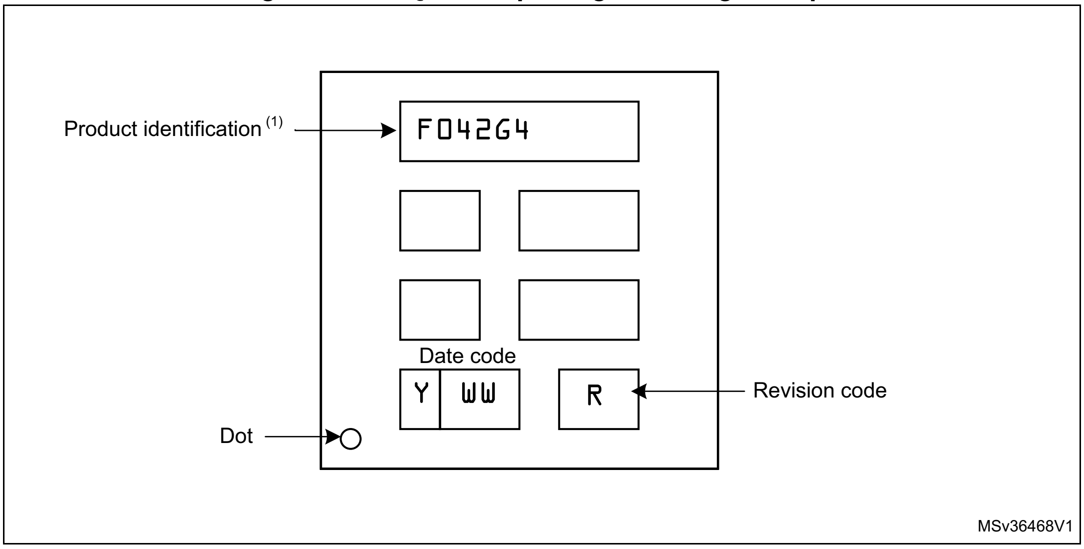
1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. This pad is used for the device ground and must be connected. It is referred to as pin 0 in *Table: Pin definitions*.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 50. UFQFPN28 package marking example



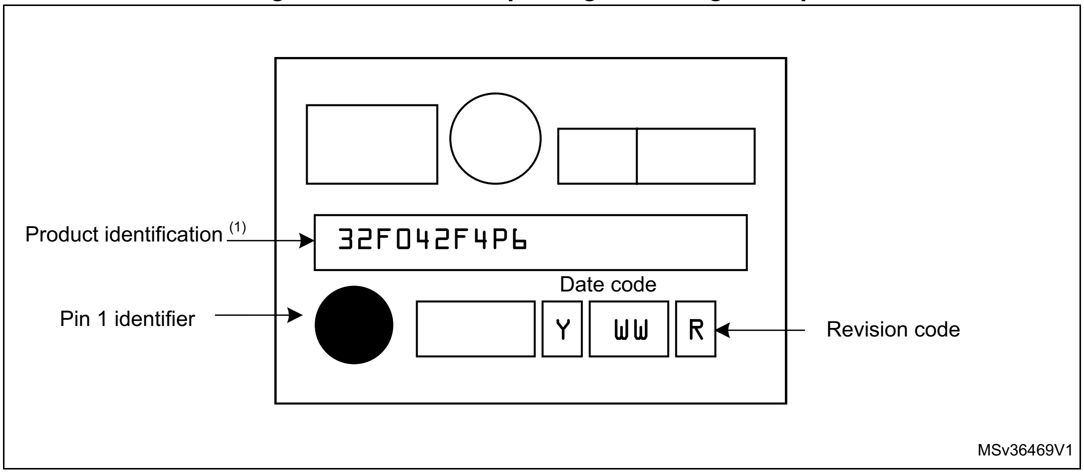
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 53. TSSOP20 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.